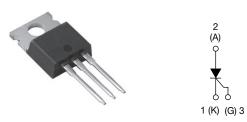


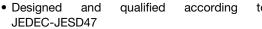
# Thyristor High Voltage, Phase Control SCR, 10 A



**TO-220AB** 

PRODUCT SUMMARY					
Package TO-220AB					
Diode variation	Single SCR				
I <sub>T(AV)</sub>	6.5 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V				
V <sub>TM</sub>	1.15 V				
I <sub>GT</sub>	15 mA				
TJ	- 40 °C to 125 °C				

#### **FEATURES**





Compliant to RoHS Directive 2002/95/EC

# RoHS

## **APPLICATIONS**

 Typical applications are in input rectification and crow-bar (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

## **DESCRIPTION**

The VS-10TTS08PbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS						
Capacitive input filter T <sub>A</sub> = 55 °C, T <sub>J</sub> = 125 °C, common heatsink of 1 °C/W	13.5	17	А			

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	RAMETER TEST CONDITIONS VALUES U						
I <sub>T(AV)</sub>	Sinusoidal waveform	6.5	^				
I <sub>T(RMS)</sub>		10	Α				
V <sub>RRM</sub> /V <sub>DRM</sub>		800	V				
I <sub>TSM</sub>		140	А				
V <sub>T</sub>	6.5 A, T <sub>J</sub> = 25 °C	1.15	V				
dV/dt		150	V/µs				
dl/dt		100	A/μs				
T <sub>J</sub>	Range	- 40 to 125	°C				

VOLTAGE RATINGS								
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA					
VS-10TTS08PbF	800	800	1.0					



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current	I <sub>T(AV)</sub>	T 110 °C 100°	ations half aire access	6.5		
Maximum RMS on-state current	I <sub>T(RMS)</sub>	T <sub>C</sub> = 112 °C, 180° conduc	ction haif sine wave	10		
Maximum peak, one-cycle,		10 ms sine pulse, rated V	<sub>RRM</sub> applied, T <sub>J</sub> = 125 °C	120	Α	
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no volta	age reapplied, T <sub>J</sub> = 125 °C	140		
Manipular 121 for fraing	I <sup>2</sup> t	10 ms sine pulse, rated V	<sub>RRM</sub> applied, T <sub>J</sub> = 125 °C	72	• 2	
Maximum I <sup>2</sup> t for fusing	I-τ	10 ms sine pulse, no voltage reapplied, T <sub>J</sub> = 125 °C		100	- A <sup>2</sup> s	
Maximum I <sup>2</sup> √t for fusing	l²√t	t = 0.1 ms to 10 ms, no vo	$t = 0.1$ ms to 10 ms, no voltage reapplied, $T_J = 125$ °C			
Maximum on-state voltage drop	$V_{TM}$	6.5 A, T <sub>J</sub> = 25 °C	1.15	V		
On-state slope resistance	r <sub>t</sub>	T 405.00		17.3	mΩ	
Threshold voltage	V <sub>T(TO)</sub>	- T <sub>J</sub> = 125 °C		0.85	V	
Maximum reverse and direct leakage	1 /	T <sub>J</sub> = 25 °C	V Datad V A	0.05		
current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$		A	
Typical holding current	I <sub>H</sub>	Anode supply = 6 V, res	30	mA		
Maximum latching current	ΙL	Anode supply = 6 V, res	50			
Maximum rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = 25 °C	150	V/µs		
Maximum rate of rise of turned-on current	dl/dt		100	A/µs		

TRIGGERING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum peak gate power	P <sub>GM</sub>		8.0				
Maximum average gate power	P <sub>G(AV)</sub>		2.0	W			
Maximum peak positive gate current	+l <sub>GM</sub>		1.5	Α			
Maximum peak negative gate voltage	-V <sub>GM</sub>		10	V			
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	20	mA			
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	15				
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	10				
Manipulation and antiqued DC make	V <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 65 °C	1.2				
Maximum required DC gate voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	1				
voltage to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	0.7	V			
Maximum DC gate voltage not to trigger	$V_{GD}$	T <sub>.I</sub> = 125 °C, V <sub>DRM</sub> = Rated value	0.2				
Maximum DC gate current not to trigger	I <sub>GD</sub>	ij = 125 C, v <sub>DRM</sub> = nated value	0.1	mA			

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.8			
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.1</sub> = 125 °C	3	μs		
Typical turn-off time	t <sub>q</sub>	1j = 125 C	100			



# www.vishay.com Vishay Semiconductors

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 125	°C	
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation	1.5		
Maximum thermal resistance, junction to ambient		R <sub>thJA</sub>		62	°C/W	
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	oz.	
Mounting torque	minimum			6 (5)	kgf · cm	
Mounting torque	maximum			12 (10)	(lbf · in)	
Marking device Case style TO-220AB 10T		10TTS	308			

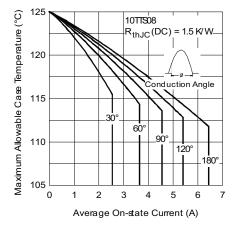


Fig. 1 - Current Rating Characteristics

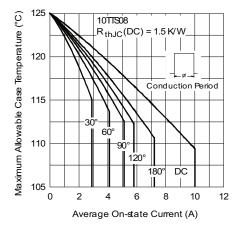


Fig. 2 - Current Rating Characteristic

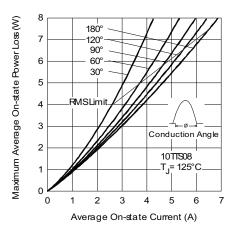


Fig. 3 - On-State Power Loss Characteristics

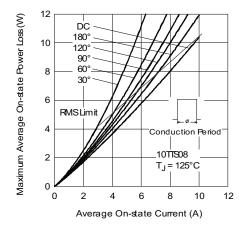


Fig. 4 - On-State Power Loss Characteristics

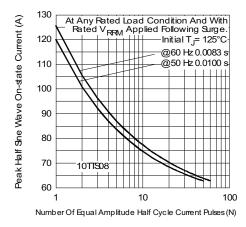


Fig. 5 - Maximum Non-Repetitive Surge Current

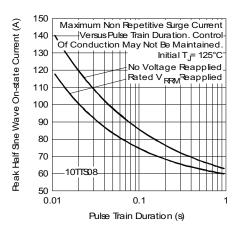


Fig. 6 - Maximum Non-Repetitive Surge Current

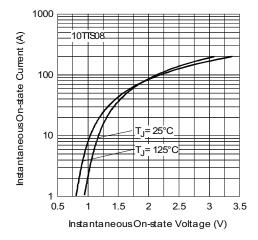


Fig. 7 - On-State Voltage Drop Characteristics

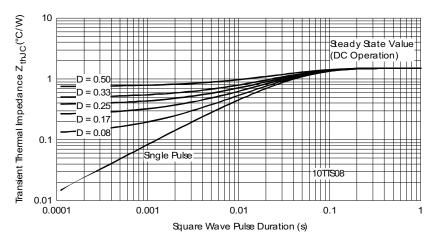
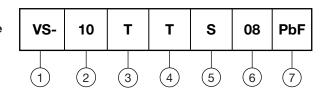


Fig. 8 - Thermal Impedance ZthJC Characteristics



#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = Converter grade

6 - Voltage code x 100 = V<sub>RRM</sub>

- • None = Standard production

• PbF = Lead (Pb)-free and RoHS compliant

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95222					
Part marking information	www.vishay.com/doc?95225				



## **TO-220AB**

#### **DIMENSIONS** in millimeters and inches



## Lead assignments

## **Diodes**

- 1. Anode/open
- 2. Cathode
- 3. Anode

#### Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	MILLIMETERS		INCHES	
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° t	o 93°	
		•	•	•	

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip



## **Legal Disclaimer Notice**

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